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STTH16R04C

Ultrafast recovery diode

Main product characteristics

I _{F(AV)}	2 X 8 A
V _{RRM}	400 V
Tj	175° C
V _{F (typ)}	0.9 V
t _{rr (typ)}	25 ns

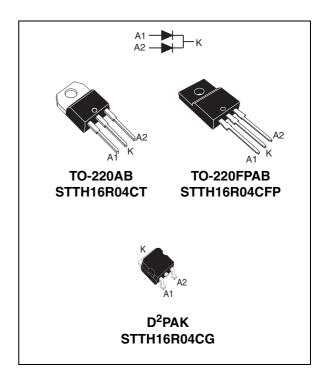
Features and benefits

- Very low switching losses
- High frequency and/or high pulsed current operation
- High junction temperature
- Insulated package:
 - TO-220FPAB
 Electrical insulation = 1500 V_{RMS}
 Capacitance = 12 pF

Description

The STTH16R04C series uses ST's new 400 V planar Pt doping technology. The STTH16R04C is specially suited for switching mode base drive and transistor circuits.

Packaged in through-the-hole and surface mount packages, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection.



Order codes

Part Number	Marking
STTH16R04CT	STTH16R04CT
STTH16R04CG	STTH16R04CG
STTH16R04CG-TR	STTH16R04CG
STTH16R04CFP	STTH16R04CFP

Characteristics STTH16R04C

1 Characteristics

Table 1. Absolute ratings (limiting values at 25° C, unless otherwise specified)

Symbol	Parameter			Value	Unit	
V _{RRM}	Repetitive peak reverse voltage			400	V	
I _{F(RMS)}	RMS forward current			30	Α	
		TO-220AB / D ² PAK	Per diode T _c = 150° C	8		
A	Average ferward ourrent S = 0.5	10-220AB / D FAR	Per device T _c = 145° C	16	Α	
'F(AV)	$I_{F(AV)}$ Average forward current, $\delta = 0.5$	TO-220FPAB	Per diode T _c = 125° C	8	A	
		Per device T _c = 90° C		16		
I _{FSM}	Surge non repetitive forward current	forward current t _p = 10 ms Sinusoidal			Α	
T _{stg}	Storage temperature range			-65 to +175	° C	
T _j	Maximum operating junction temperature range			-40 to +175	°C	

Table 2. Thermal parameters

Symbol	Parameter			Value	Unit
R _{th(j-c)}	Junction to case	TO-220AC / D ² PAK	Per diode	2	°C/W
			Per device	1.15	
		TO-220FPAB	Per diode	4.6	
			per device	3.8	
R _{th(c)}	Coupling	TO-220AC / D ² PAK	Per device	0.3	°C/W
		TO-220FPAB	per device	3	C/VV

When the diodes are used simultaneously:

$$\Delta T_{j(diode\ 1)} = P_{(diode\ 1)}\ x\ R_{th(j-c)(Per\ diode)} + P_{(diode\ 2)}\ x\ R_{th(c)}$$

STTH16R04C Characteristics

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min	Тур	Max	Unit
I _R ⁽¹⁾	I Beverse leakane current	T _j = 25° C	V V			10	μΑ
'R`		T _j = 125° C	$V_R = V_{RRM}$		10	100	
V _F ⁽²⁾ Fo	Forward voltage drop	T _j = 25° C	I _F = 8 A			1.5	
		T _j = 100° C			1.05	1.3	
		T _j = 150° C			0.9	1.1	V
		T _j = 25° C				1.75	v
		T _j = 100° C	I _F = 16 A		1.25	1.55	
		T _j = 150° C			1.12	1.37	

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2$ %

To evaluate the conduction losses use the following equation: P = 0.83 x $\rm I_{F(AV)}$ + 0.034 x $\rm I_{F}{}^{2}_{(RMS)}$

Dynamic characteristics Table 4.

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
t _{rr} Reverse recovery time	Deverse receivant time	$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		35	50	ns
	$I_F = 1 \text{ A, } dI_F/dt = -100 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		25	35	115	
I _{RM}	Reverse recovery current	$I_F = 8 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s},$ $V_R = 320 \text{ V}, T_j = 125^{\circ} \text{ C}$		5.5	8	Α
S	Softness factor	$I_F = 8 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s}, \ V_R = 320 \text{ V}, T_j = 125^{\circ} \text{ C}$		0.4		
t _{fr}	Forward recovery time	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}, T_j = 25^{\circ} \text{ C}$			150	ns
V _{FP}	Forward recovery voltage	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$ $T_j = 25^{\circ} \text{ C}$		2.9		V

^{2.} Pulse test: t_p = 380 μ s, δ < 2 %

Characteristics STTH16R04C

Figure 1. Conduction losses versus average current

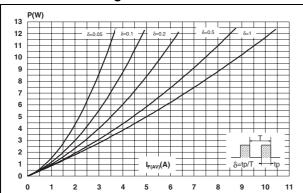


Figure 2. Forward voltage drop versus forward current

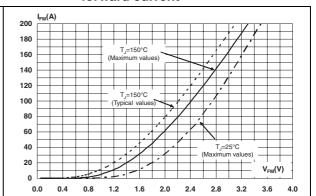
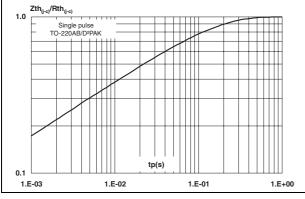


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Relative variation of thermal impedance junction to case versus pulse duration TO-220FPAB



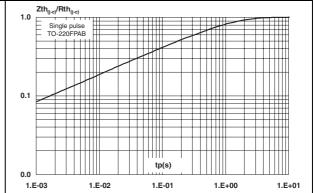
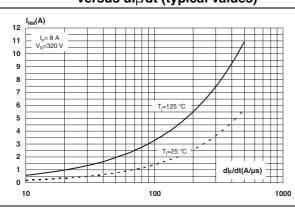
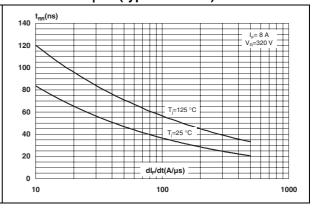


Figure 5. Peak reverse recovery current versus dl_F/dt (typical values)



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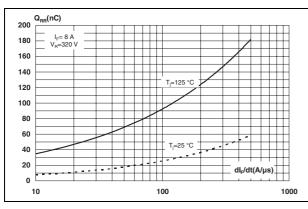
Figure 6. Reverse recovery time versus dl_F/dt (typical values)



STTH16R04C Characteristics

Figure 7. Reverse recovery charges versus dl_F/dt (typical values)

Figure 8. Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, e_{CU} = 35 μ m)



Rth₍₃₋₃₎(°C/W)

80

70

60

40

30

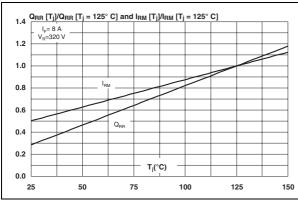
20

10

0 2 4 6 8 10 12 14 16 18 20

Figure 9. Relative variations of dynamic parameters versus junction temperature

Figure 10. Transient peak forward voltage versus dl_F/dt (typical values)



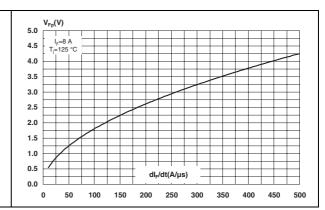
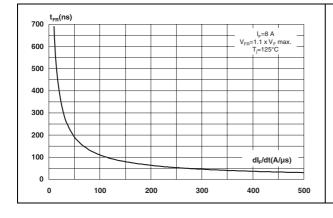
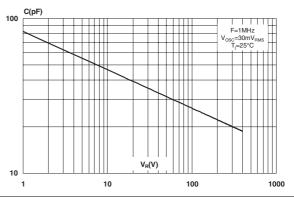


Figure 11. Forward recovery time versus dl_F/dt Figure 12. (typical values)

Junction capacitance versus reverse voltage applied (typical values)





Package information STTH16R04C

2 Package information

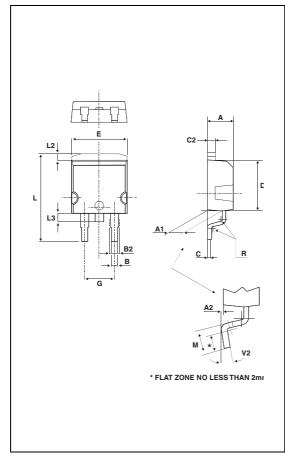
Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.8 Nm (TO-220FPAB) / 0.55 Nm (TO-220AB)

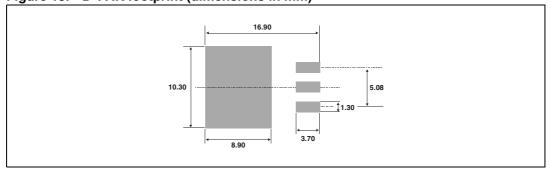
Maximum torque value: 1.0 Nm (TO-220FPAB) / 0.70 Nm (TO-220AB)

Table 5. D²PAK dimensions



	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.49	2.69	0.098	0.106	
A2	0.03	0.23	0.001	0.009	
В	0.70	0.93	0.027	0.037	
B2	1.14	1.70	0.045	0.067	
С	0.45	0.60	0.017	0.024	
C2	1.23	1.36	0.048	0.054	
D	8.95	9.35	0.352	0.368	
Е	10.00	10.40	0.393	0.409	
G	4.88	5.28	0.192	0.208	
L	15.00	15.85	0.590	0.624	
L2	1.27	1.40	0.050	0.055	
L3	1.40	1.75	0.055	0.069	
М	2.40	3.20	0.094	0.126	
R	0.40 typ.		0.016	6 typ.	
V2	0°	8°	0°	8°	

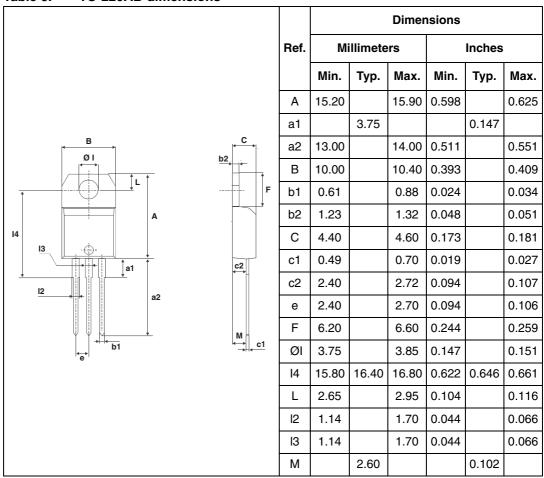
Figure 13. D²PAK footprint (dimensions in mm)



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STTH16R04C Package information

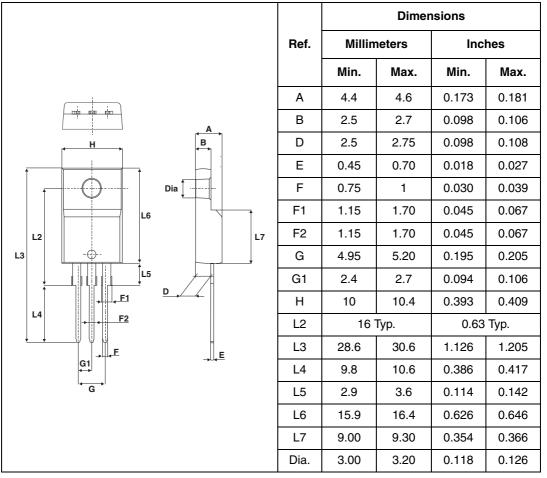
Table 6. TO-220AB dimensions



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Package information STTH16R04C

Table 7. TO-220FPAB dimensions



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

3 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH16R04CT	STTH16R04CT	TO-220AB	1.92 g	50	Tube
STTH16R04CG	STTH16R04CG	D ² PAK	1.48 g	50	Tube
STTH16R04CG-TR	STTH16R04CG	D ² PAK	1.48 g	1000	Tape and reel
STTH16R04CFP	STTH16R04CFP	TO-220FPAB	1.69 g	50	Tube

4 Revision history

Date	Revision	Description of Changes
31-Mar-2007	1	First issue

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